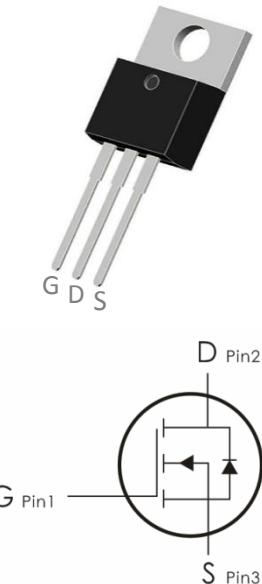


## Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent  $R_{DS(on)}$  with low gate charge. It can be used in a wide variety of applications.

## Features:

- 1)  $V_{DS}=60V, I_D=50A, R_{DS(on)}<22m\Omega @ V_{GS}=10V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra  $R_{DS(on)}$ .
- 5) Excellent package for good heat dissipation.



## Absolute Maximum Ratings: ( $T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
$V_{DS}$	Drain-Source Voltage	60	V
$V_{GS}$	Gate-Source Voltage	$\pm 20$	V
$I_D$	Continuous Drain Current-	50	A
	Continuous Drain Current- $T_C=100^\circ C$	35.4	
	Pulsed Drain Current	200	
$E_{AS}$	Single Pulse Avalanche Energy	490	mJ
$P_D$	Power Dissipation	120	W
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ C$

**Electrical Characteristics:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
<b><math>\text{BV}_{\text{DSS}}</math></b>	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_D=250 \mu\text{A}$	60	---	---	V
<b><math>I_{\text{DSS}}</math></b>	Zero Gate Voltage Drain Current	$V_{\text{GS}}=0\text{V}, V_{\text{DS}}=60\text{V}$	---	---	1	$\mu\text{A}$
<b><math>I_{\text{GSS}}</math></b>	Gate-Source Leakage Current	$V_{\text{GS}}=\pm 20\text{V}, V_{\text{DS}}=0\text{A}$	---	---	$\pm 100$	nA
<b>On Characteristics</b>						
<b><math>V_{\text{GS(th)}}</math></b>	GATE-Source Threshold Voltage	$V_{\text{GS}}=V_{\text{DS}}, I_D=250 \mu\text{A}$	2	---	4	V
<b><math>R_{\text{DS(ON)}}</math></b>	Drain-Source On Resistance	$V_{\text{GS}}=10\text{V}, I_D=70\text{A}$	---	18	22	$\text{m}\Omega$
<b>Dynamic Characteristics</b>						
<b><math>C_{\text{iss}}</math></b>	Input Capacitance	$V_{\text{DS}}=25\text{V}, V_{\text{GS}}=0\text{V}, f=1\text{MHz}$	---	1050	1365	pF
<b><math>C_{\text{oss}}</math></b>	Output Capacitance		---	460	600	
<b><math>C_{\text{rss}}</math></b>	Reverse Transfer Capacitance		---	70	90	
<b>Switching Characteristics</b>						
<b><math>t_{\text{d(on)}}</math></b>	Turn-On Delay Time	$V_{\text{DD}}=30\text{V}, I_D=25\text{A}, R_{\text{GEN}}=25 \Omega$ .	---	20	50	ns
<b><math>t_r</math></b>	Rise Time		---	100	210	ns
<b><math>t_{\text{d(off)}}</math></b>	Turn-Off Delay Time		---	80	170	ns
<b><math>t_f</math></b>	Fall Time		---	85	180	ns
<b><math>Q_g</math></b>	Total Gate Charge	$V_{\text{GS}}=10\text{V}, V_{\text{DS}}=48\text{V}, I_D=50\text{A}$	---	32	42	nC

**Typical Characteristics:** ( $T_C=25^\circ\text{C}$  unless otherwise noted)
